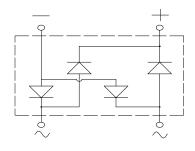


Fast Recovery Bridge Rectifiers





Features

- UL recognition, file #E313149
- Glass passivated chip junction
- Ideal for automated placement
- High surge current capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

Typical Applications

General purpose use in AC/DC bridge full wave rectification for SMPS, lighting ballaster, adapter, battery charger, home appliances, office equipment, and telecommunication applications.

Mechanical Data

Package: YBS2G
 Molding compound meets UL 94 V-0 flammability rating, -compliant, Halogen-free

• **Terminals**: Tin plated leads, solderable per J-STD-002 and JESD22-B102

• Polarity: As marked on body

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	RYBSA2010
Device marking code			RYBSA2010
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	V	1000
Maximum RMS Voltage	V_{RMS}	V	700
Maximum DC blocking Voltage	V _{DC}	V	1000
Average rectified output current @60Hz sine wave, R-load, Tc=100°C	Io	А	2.0
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave,1 cycle, Tj=25°C		А	75
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, Tj=25°C	I _{FSM}		150
Current squared time @1ms≤t≤8.3ms Tj=25°C, Rating of per diode	l ² t	A ² s	23.3
Storage temperature	T _{stg}	℃	-55 ~ + 150
Junction temperature	Тј	°C	-55 ~ + 150



■Electrical Characteristics (Ta=25°C Unless otherwise specified)

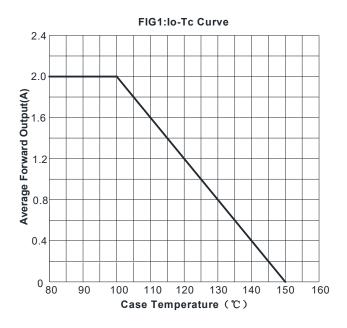
PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	RYBSA2010
Maximum reverse recovery time	t _{rr}	ns	I _F =0.5A,I _R =1.0A, I _{rr} =0.25A	500
Maximum instantaneous forward voltage drop per diode	V_{F}	V	I _{FM} =1.0A	1.3
Maximum DC reverse current at rated DC blocking voltage per diode	I _R	μΑ	Tj =25℃	5
			Tj =125°C	100
Typical junction capacitance	Cj	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	

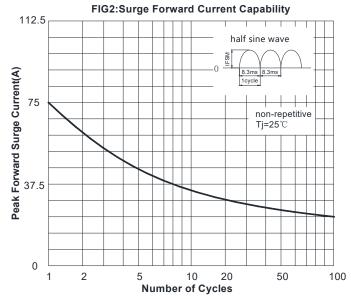
■Thermal Characteristics $(T_a=25 \degree C \text{ Unless otherwise specified})$

	PARAMETER	SYMBOL	UNIT	RYBSA2010
	Between Junction and Ambient	$R_{\theta J-A}$		50
Typical Thermal Resistance	Between Junction and Lead	R _{θJ-L}	°C/W	11
	Between Junction and Case	$R_{\theta J-C}$		7

Note: Device mounted on P.C.B with 35mm*25mm*1.7mm.

■ Characteristics (Typical)







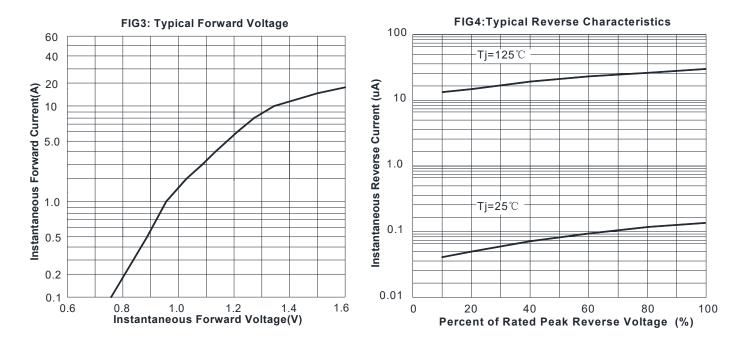
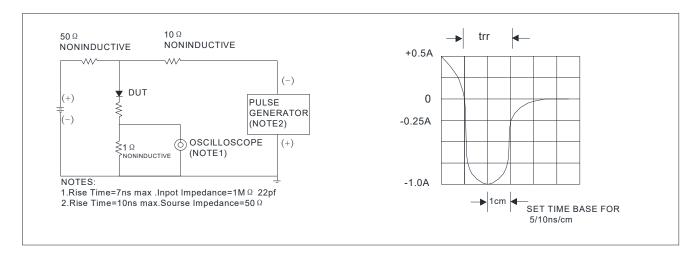
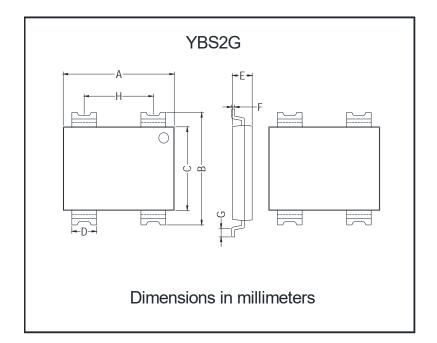


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time



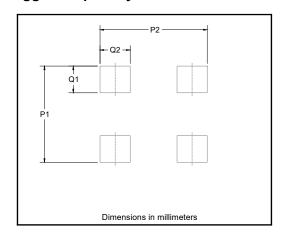


■ Outline Dimensions



YBS2G				
Dim	Min	Max		
Α	8.6	9.2		
В	8.3	8.9		
С	6.2	6.6		
D	1.85	2.15		
E	1.35	1.75		
F	0.1	0.3		
G	0.4	0.8		
Н	5.4	5.8		

■ Suggested pad layout



YBS2G		
Dim	Min	
P1	11	
P2	7.8	
Q1	2.4	
02	2.2	



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